

2SD468

NPN Silicon Epitaxial Planar Transistor

Low Frequency Power amplifier applications.

The transistor is subdivided into two groups B and C according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	25	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Peak Collector Current	I_{CM}	1.5	A
Power Dissipation	P_{tot}	0.9	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 0.5\text{ A}$ Current Gain Group B C	h_{FE}	85	-	170	-
	h_{FE}	120	-	240	-
Collector Base Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	1	μA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	25	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 0.8\text{ A}$, $I_B = 0.08\text{ A}$	$V_{CE(sat)}$	-	0.2	0.5	V
Base Emitter Voltage at $V_{CE} = 2\text{ V}$, $I_C = 0.5\text{ A}$	V_{BE}	-	0.79	1	V
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	22	-	pF
Transition Frequency at $V_{CE} = 2\text{ V}$, $I_C = 0.5\text{ A}$	f_T	-	190	-	MHz



